

Dielectric environment mediated quantum screening of one dimensional electron gas

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Relaxing the assumption of “infinite and homogenous background” the dielectric response function of one-dimensional (1D) semiconducting nanowires embedded in a dielectric environment is calculated. It is shown that high- κ (higher than semiconductor dielectric constant) dielectric environment reduces the screening by the free carriers inside the nanostructure whereas, low dielectric environment increases the Coulombic interaction between free carriers and enhances the strength of screening function. In long wavelength limit, dielectric screening and collective excitation of electron gas are found to be solely determined by the environment instead of the semiconductor. Behavior of static dielectric function is particularly addressed at a specific wavevector $q = 2k_F$; a wavevector ubiquitously appears in charge transport in nanostructures.

Low-dimensional structures such as semiconducting nanowires (1D) are being investigated intensively for their potential applications in high-speed electronic and optical devices¹. These semiconducting nanowires either can be freestanding or can be coated with different dielectric environment appropriate to device application. For example, in nanowire-based field effect transistors (FET), wires are usually coated with high- κ dielectrics (HfO₂, ZrO₂ etc.)² for improved charge control as well as for high electron mobility³. On the other hand, for exciton-based devices, use of low- κ (lower than semiconductor dielectric constant ϵ_s) dielectric is beneficial as it enhances excitonic binding energy⁴. These advantages in electronic and optical properties stems out from the fact that the Coulombic interaction between carrier and/or impurities inside the nanowires can be altered by altering the environment. This tunability of the carrier-carrier interaction by dielectric environment is expected to modify many body effects such as dielectric screening by one dimensional electron gas (1DEG) inside the nanowire.

Dielectric screening by free carriers plays a crucial role in determination of transport quantities (conductivity, mobility, etc) of a nanostructure. In a scattering event, the momentum-relaxation time (τ) strongly ($\tau \sim |\epsilon(q, 0)|^{-2}$) depends on the free electron screening inside the semiconductor. Hence an accurate knowledge of dielectric screening is necessary for a precise prediction of transport coefficients of a nanowire. The dielectric function of a semiconductor nanowire is composed of i) ionic (ϵ^{ion}) and ii) electronic (ϵ^{ele}) contributions. ϵ^{ion} is an inherent property (crystal property) of semiconductors, while ϵ^{el} (commonly known as screening function) depends on the magnitude of the

electron-electron interaction inside a material. As dielectric environment can alter the Coulomb potential inside a nanowire, it is expected that dielectric environment will have a pronounced effect of the free electron screening of the nanowire⁵. Previous models⁶⁻⁹ for dielectric function of 1DEG assumes that the electron gas has an infinite homogenous background having dielectric constant (ϵ_s) same as the semiconductor. For a nanowire of few nm radius, “infinite background” approximation certainly breaks down and at the nanowire/environment interface “homogenous background” assumption fails. In this work, assumption “infinite homogenous background” is relaxed, and incorporating dielectric mismatch factor at the nanowire/environment a consistent theory of dielectric function is developed using the method of “self consistent field”¹⁰ (also known as random-phase approximation or RPA).

We consider an infinitely long semiconductor wire (dielectric constant ϵ_s) of a radius (R) few nanometers embedded in a dielectric (dielectric constant ϵ_e) environment. To investigate the dielectric response of the electron gas inside the wire, we place an oscillating test charge at $(\mathbf{r}_0, z_0) = (0, 0)$ of density $n_0(r, t) = e\delta(\mathbf{r})e^{-i\omega t}$. This test charge creates a longitudinal electric field $V_0(r, z)e^{-i\omega t}$ in the nanowire and in response to this perturbation, free electrons inside the nanowire rearrange themselves to screen the field. The resultant Hamiltonian of electrons confined in the wire is $H = H_0 + V(\mathbf{r}, t)$, where $V(\mathbf{r}, t)$ is the self-consistent potential in response to the external perturbation $V_0(\mathbf{r}, t)$. The unperturbed single-particle Hamiltonian $H_0 = \mathbf{p}^2/2m^* + V_{con}(r)$ satisfy Schroedinger equation $H_0|n, k\rangle = \mathcal{E}_{n,k}|n, k\rangle$. Here m^* is the effective mass of electron, k is the one dimensional wave vector, $|n, k\rangle$ and $\mathcal{E}_{n,k}$ are the eigenvectors and eigen-energy of the unperturbed Hamiltonian and $V_{con}(r)$ is the confinement potential for electrons inside the nanowire. Assuming electrons are confined in an infinite-barrier potential, the eigen-energies are $\mathcal{E}_{n,k} = \mathcal{E}_n + \hbar^2 k^2/2m^*$, where \mathcal{E}_n is the ground

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83 state energy of the n th 1D subband and \hbar is the re-
 84 duced Planck constant. The corresponding wavefunc-
 85 tion is $\Psi_{n,k}(r, z) = \langle r|n, k \rangle = \phi_n(r) \cdot [\exp(ikz)/\sqrt{L}]$,
 86 where $\phi_n(r)$ is the radial part and L is the length of
 87 the nanowire. The dielectric function of an electron gas
 88 is defined by the relation¹¹

$$V_{nn'} = \sum_{mm'} \epsilon_{nn',mm'}^{-1}(q, \omega) V_{mm'}^0, \quad (1)$$

89 where $\epsilon_{nn',mm'}^{-1}(q, \omega)$ is the four dimensional dielectric
 90 matrix and $V_{ij}^0(V_{ij}^0) = \langle j, k + q | V(V_0) | i, k \rangle$ are the tran-
 91 sition matrix element between states $|i, k\rangle$ and $|j, k + q\rangle$.
 92 Diagonal elements of the dielectric matrix represent the
 93 intrasubband polarization of the 1DEG whereas, the off-
 94 diagonal terms coming from inter-subband transitions.
 95 In size quantum limit (SQL) of nanowire, when carriers
 96 are confined in the lowest ground state and intersubband
 97 separation is large, dielectric function becomes a scalar
 98 quantity.

99 The self-consistent potential contains both original
 100 perturbation as well as the screened potential by the mo-
 101 bile charges, i.e. $V(\mathbf{r}, t) = V_0(\mathbf{r}, t) + V_s(\mathbf{r}, t)$. For the
 102 evaluation of the dielectric response of a 1D electron gas,
 103 it is imperative to calculate the screening potential V_s
 104 (see eq. 1)). The self-consistent potential $V(\mathbf{r}, t)$, upon
 105 acting on state $|n, k\rangle$ mixes in other state such that wave
 106 function becomes $\Psi(r, t) = |n, k\rangle + b_{k+q}(t) |n', k + q\rangle$. The
 107 coefficient $b_{k,k+q}(t)$ is given by time dependent perturba-
 108 tion theory¹²

$$b_{k,k+q}(t) = \frac{V_{nn'}(q) e^{-i\omega t}}{\mathcal{E}_{n'}(k+q) - \mathcal{E}_n(k) - \hbar\omega}, \quad (2)$$

109 where, $V_{nn'} = \langle n', k + q | V | n, k \rangle$ is the matrix el-
 110 ement between state $|n, k\rangle$ and $|n', k + q\rangle$. The
 111 perturbation-induced charge density is $n^{ind}(r, t, z) =$
 112 $-2e \sum_{k,nn'} f_n^0(k) [|\Psi(r, t)|^2 - |\Psi_{n,k}(r, z)|^2]$, where, e
 113 is the charge of an electron and $f_n^0(k)$ denotes the
 114 equilibrium Fermi-Dirac occupation probability of a
 115 state $|n, k\rangle$ such that $2 \sum_{n,k} f_n^0(k) = n_{1d}$, n_{1d} be-
 116 ing the equilibrium homogeneous unperturbed elec-
 117 tron gas density. Assuming that the perturba-
 118 tion is weak enough such that response is linear
 119 and neglecting terms $b_{n,k+q}^2$ and higher orders, in-
 120 duced charge density can be written as $n^{ind}(r, t) =$
 121 $-e \sum_{nn'} \phi_n(r) \phi_{n'}(r) V_{nn'} \mathcal{F}_{nn'}(q, \omega) e^{iqz} e^{i\omega t}$, where
 122 $\mathcal{F}_{nn'}(q, \omega)$ is the polarization function¹² (Lindhard func-
 123 tion) obtained by summing the Feynman diagram of
 124 electron-electron interaction containing single fermion
 125 loop^{6,13},

$$\mathcal{F}_{nn'}(q, \omega) = \frac{2}{L} \sum_k \frac{f_n^0(k) - f_{n'}^0(k+q)}{\mathcal{E}_{n'}(k+q) - \mathcal{E}_n(k) - \hbar\omega}. \quad (3)$$

126 Note that, the induced charge density has the same har-
 127 monic dependence as the self consistent potential. The
 128 induced charge density is related to the screening po-
 129 tential by Poisson's equation $\nabla^2 V_s(\mathbf{r}) = -n^{ind}(\mathbf{r})/\epsilon_0\epsilon_s$,

130 where ϵ_0 is the free-space permittivity. Expressing
 131 screening potential in Fourier components $V_s(r, z) =$
 132 $\sum_{-\infty}^{\infty} v_s(r, q) e^{iqz}$, where $q = k' - k$, one obtain the dif-
 133 ferential equation for the screening potential

$$\frac{1}{r} \frac{d}{dr} \left(r \frac{dv_s}{dr} \right) - q^2 v_s = \begin{cases} -n^{ind}(r)/\epsilon_0\epsilon_s, & r \leq R \\ 0, & r \geq R. \end{cases} \quad (4)$$

134 The Green's function appropriate to above differential
 135 equation with dielectric mismatch effect is^{3,14}

$$G(r, r', q) = \frac{1}{\pi} \left[\underbrace{I_0(qr_{<}) K_0(qr_{>})}_{g^{inhom}(r, r')} + \underbrace{\mathcal{U}(qR) I_0(qr) K_0(qr')}_{g^{hom}(r, r')} \right]$$

$$\mathcal{U}(x) = \frac{(\epsilon_s - \epsilon_e) K_0(x) K_1(x)}{\epsilon_e I_0(x) K_1(x) + \epsilon_s I_1(x) K_0(x)} \quad (5)$$

136 where, $g^{hom}(inhom)(r, r')$ is the homogenous
 137 (inhomogenous) part of the Green's function,
 138 $r_{<(>)} = \min(\max)[r, r']$, $I_n(\dots)$ and $K_n(\dots)$ are the
 139 n th order modified Bessel functions. For large x
 140 ($x > \sqrt{n^2 - 1}$), $I_n(x) \approx e^x/\sqrt{2\pi x}$, $K_n(x) \approx e^{-x}\sqrt{2\pi/x}$
 141 and the function $\mathcal{U}(qR) \rightarrow (\pi\gamma/2)e^{-2qR}$, where
 142 $\gamma = (\epsilon_s - \epsilon_e)/(\epsilon_s + \epsilon_e)$ is the dielectric mismatch factor.
 143 The tunability of the strength of the Green's function
 144 comes through its dependence on γ , which enhances
 145 (reduces) the strength for $\epsilon_s > \epsilon_e$ ($\epsilon_s < \epsilon_e$). For an
 146 infinite homogeneous environment ($\epsilon_e = \epsilon_s$), $\gamma = 0$, and
 147 the Green's function is independent of the dielectric
 148 environment. Using the above Green's function, the
 149 induced potential inside the nanowire can be written
 150 as $v_s(r, q) = e^2/4\pi\epsilon_0\epsilon_s \int_0^R G(r, r', q) n^{ind}(r') r' dr'$ ¹⁵. In
 151 the size quantum limit (SQL), the nanowire is thin,
 152 ($R < \lambda_{dB}$, λ_{dB} is de Broglie wavelength of an electron)
 153 and only the lowest subband is populated. Moreover,
 154 for a thin nanowire, inter-subband separation energy is
 155 large ($\Delta\mathcal{E}_n \propto 1/R^2$) such that inter-subband transition
 156 can be neglected ($n = n' = 1$). In such a scenario
 157 (SQL limit), the dielectric matrix becomes scalar, i.e.
 158 $\epsilon_{nn'}(q, \omega) \rightarrow \epsilon_{11}(q, \omega)$. Assuming $\phi_{n=1}(r) \approx 1/\sqrt{\pi R^2}$,
 159 the dynamic dielectric function of an 1DEG at tempera-
 160 ture $T = 0$ is¹⁶

$$\epsilon_{1d}(q, \omega, \mathcal{E}_F) = 1 - \frac{e^2}{4\pi\epsilon_0\epsilon_s V_{11}} \int_0^R \phi_1^2(r) r \int_0^R G(r, r') n^{ind}(r') r' dr' dr$$

$$= 1 + \frac{1}{\pi a_B^* R^2} \frac{F(x)}{q^3} \ln \left| \frac{(q + 2k_F)^2 - (\frac{2m^* \omega}{\hbar q})^2}{(q - 2k_F)^2 - (\frac{2m^* \omega}{\hbar q})^2} \right| \quad (6)$$

161 where $x = qR$ a dimensionless quantity, $F(x) = \left[\frac{1}{2} + \right.$
 162 $\left. I_1(x) [\mathcal{U}(x) I_1(x) - K_1(x)] \right]$, $a_B^* = 4\pi\epsilon_0\epsilon_s/m^*e^2$ is the
 163 effective bulk Bohr radius, $k_F = \pi n_{1d}/2$ is the Fermi
 164 wavevector and $\mathcal{E}_F = \hbar^2 k_F^2/(2m^*)$ is the corresponding
 165 Fermi energy. The logarithmic term in Eq.6 is arising
 166 from the Lindhard function $\mathcal{F}_{11}(q, \omega)$ which has been
 167 evaluated analytically in SQL⁶. In the context of charge
 168 transport inside the nanowire, static dielectric function
 169 $\epsilon_{1d}(q, \omega = 0)$ is relevant than dynamic one. In the long

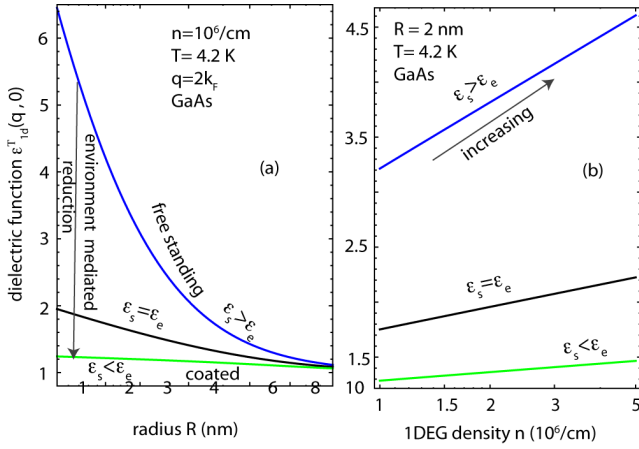


FIG. 1. dielectric function of a nanowire a) with nanowire radius (R) and b) as a function of carrier density (n) for three different dielectric environments of $\epsilon_e = 1$ (upper branch), $\epsilon_e = \epsilon_s = 13$ (middle) and $\epsilon_e = 100$ (lower branch).

171 wavelength ($q \ll 2k_F$) limit, static dielectric function
172 $\epsilon_{1d}(q, 0)$ for a thin nanowire ($qR \rightarrow 0$) is

$$\epsilon_{1d}(q, 0) = 1 - \frac{e^2}{2\pi\epsilon_0\epsilon_e} [\ln(qR)] \mathcal{D}_{1d}(\mathcal{E}_F), \quad (7)$$

173 where, $\mathcal{D}_{1d}(\mathcal{E}_F) = 1/\pi\hbar\sqrt{2m^*/\mathcal{E}_F}$ is the 1D density of
174 states per unit length at Fermi energy \mathcal{E}_F . In sharp con-
175 trast to previous models¹¹, ϵ_e instead of ϵ_s , determines
176 the long-wavelength behavior of the static dielectric func-
177 tion.

178 For large momentum ($q \gg 2k_F$), $\epsilon_{1d}(q, 0) \rightarrow 1$ as the
179 second term of Eq. 6 falls off rapidly (q^{-5}) with q . For a
180 degenerate 1DEG in SQL, only possible way of scattering
181 is backscattering which leads to a momentum trans-
182 fer $q = 2k_F$ in any intrasubband elastic scattering pro-
183 cess. As a result, $\epsilon_{1d}(q = 2k_F, 0)$ plays an important role
184 in momentum relaxation rate calculation. In the static
185 limit ($\omega = 0$), the dielectric function $\epsilon_{1d}(q, 0)$ at $T = 0$
186 is singular for $q = 2k_F$. This divergence is related to
187 Pierl's instability which is a characteristic signature of a
188 1DEG. At finite temperature, smearing of Fermi function
189 removes this singularity. At finite temperature, the static
190 dielectric function is given by Maldague's prescription¹⁸

$$\epsilon_{1d}^T(q, 0) = \int_0^\infty d\mathcal{E} \epsilon_{1d}(q, 0, \mathcal{E}) \left[4k_B T \cosh^2 \left[\frac{\mathcal{E} - \mathcal{E}_F}{2k_B T} \right] \right] \quad (8)$$

191

192

193 Fig.1a) shows the static dielectric function of a GaAs
194 nanowire at $q = 2k_F$ with nanowire radius R for three
195 different dielectric medium. Note that even negligible
196 smearing of Fermi distribution at $T = 4.2$ K is enough to
197 remove the divergence at $q = 2k_F$. For coated nanowires
198 with $\epsilon_e > \epsilon_s$, dielectric screening is strongly reduced as
199 shown in Fig. 2 b). At large radius ($R \gg 1/4k_F$),
200 nanowire tends to the bulk structure and the dielectric

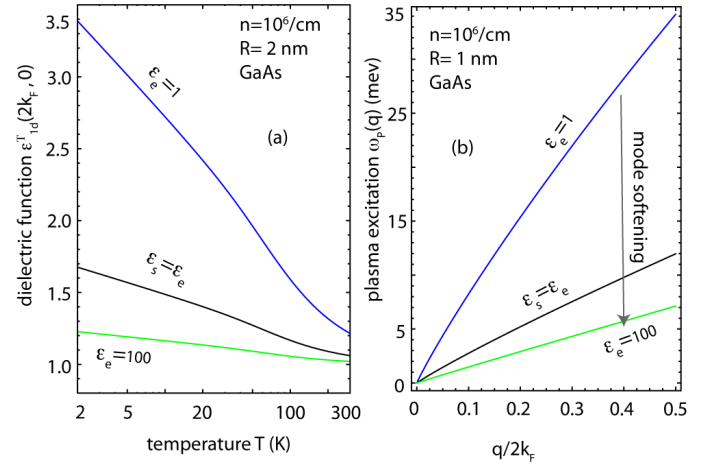


FIG. 2. a) dielectric function of a nanowire with temperature (T) and b) plasma frequency of an 1DEG with wavevector (q) for three different dielectric environments.

201 mismatch effect on the screening function vanishes. With
202 increasing carrier density, dielectric screening inside the
203 nanowire increases (see Fig. 1b) maintaining the effect of
204 dielectric environment intact. At higher carrier densities,
205 more than one subband is populated and inter-subband
206 contribution to the total dielectric function should be
207 taken account for a complete description of free electron
208 screening inside the nanowire. With increasing tempera-
209 ture, thermal fluctuation reduces the free electron screen-
210 ing inside the nanowire and the effect of environmental
211 dielectric on the screening function is partially washed
212 away (see Fig. 2a).

214 As the dynamic ($\omega \neq 0$) dielectric function $\epsilon_{1d}(q, \omega)$
215 contains the dielectric mismatch factor, collective excita-
216 tion of 1DEG is also expected to depend on the dielectric
217 environment. Collective excitation of an electron gas is
218 defined the pole of the full dynamic dielectric function,
219 i.e. by $\epsilon_{1d}(q, \omega_p) = 0$, where ω_p is the plasma frequency
220 of the electron gas. Fig.2b) shows the plasma dispersion
221 of intra-subband collective excitation of a thin nanowire
222 ($R = 2$ nm) for different dielectric environments. For
223 $q < 1/2R$, dielectric environment has finite effect on the
224 collective excitation frequency of 1DEG. The softening of
225 plasma frequency with high- ϵ_e dielectric environment is
226 the consequence of the reduction of Coulomb interaction
227 between electron and positive background, which acts
228 as a restoration force of the collective oscillation of the
229 electron gas. For small q , frequency of collective
230 excitation goes to zero for all dielectric environment
231 following the relation $\omega_p(q) \approx \omega_0 q \sqrt{-\ln(qR)}$, where
232 $\omega_0 = \sqrt{n_{1d}e^2/(4\pi\epsilon_0\epsilon_e m^*)}$. Note the explicit appearance
233 of ϵ_e in ω_0 justifies the role of environment in collective
234 excitation of 1DEG inside the wire.

235
236 The length scale at which dielectric environment plays
237 an important role can be determined by investigating
238 the behavior of $\mathcal{U}(qR)$. For large qR , $\mathcal{U}(qR) \sim e^{-4k_F R}$.

Hence for $R \gg 1/(4k_F)$, $\mathcal{U}(qR)$ becomes negligible and dielectric effect vanishes. For a numerical estimates, at carrier density $n_{1d} = 10^6$ /cm dielectric effect vanishes for $R \gg 2$ nm, whereas at lower density ($n_{1d} = 10^5$ /cm) environmental effect on quantum screening function persists for wire radius $R \approx 20$ nm.

In our work we assume an infinite confining potential for electron inside the wire. Relaxing this assumption will results in electron mass enhancement due to leaking of wavefunction into the barrier. For high- κ oxides the typical barrier height is ~ 1 eV, for which nominal increase in electron mass can be neglected¹⁷. The assumption of constant radial part of the wavefunction is justified for thin nanowires. Choosing a different form for the radial part will change the absolute value of screening function for thick (for large R dielectric environment effect ceases out anyway) wires keeping the relative effect of environments unchanged.

In conclusion, we have shown that the free electron screening inside a nanowire depends on the environment surrounding it. For a nanowire coated with high- κ dielectric, perturbation inside the nanowire is poorly screened compared to a freestanding nanowire. It is shown that both static dielectric function and plasma dispersion at long-wavelength limit gets modified by environment . We derived the length-scale at which the environment has meaningful effect on the electron gas inside the nanowire. Results are analytical and will be useful for accurate prediction of transport coefficients in nanowire-based electronic devices.

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- ⁵One such example is dielectric environment mediated free electron screening in graphehe, where an average dielectric constant of graphene $\epsilon_{gr}^{avg} = (\epsilon_e^t + \epsilon_e^b)/2$ is used in Thomas-Fermi screening function. Here $\epsilon_e^t(\epsilon_e^b)$ is the dielectric constant of top (bottom) environment of graphene and the crystal property of atomically thin (monolayer 0.3 nm) graphene is neglected. For a nanowire of radius few nm, crystal property of the semiconductor can not be neglected and a rigorous model containing both ϵ_e and ϵ_s is necessary.
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